

IN THE CLAIMS

Please amend the following claims which are pending in the present application:

31. (Twice Amended) A gate electrode comprising:
- an insulative layer disposed on a substrate;
 - a gate layer disposed on said insulative layer;
 - thin first spacers disposed adjacent to opposite sides of said gate layer;
 - thin second spacers disposed adjacent to opposite sides of said thin first spacers;
 - thin third spacers disposed adjacent to opposite sides of said thin second spacers;
 - thick fourth spacers disposed adjacent to opposite sides of said thin third spacers; and
 - a conductive layer disposed on said gate layer, extending beyond edges of said gate layer and having a lower side at least as high as upper edges of said first, second, third, and fourth spacers.
32. (Amended) The gate electrode of claim 31 wherein said insulative layer comprises an oxide.
33. (Amended) The gate electrode of claim 32 wherein said gate layer comprises a polysilicon.

34. (Amended) The gate electrode of claim 33 wherein said conductive layer comprises a polycide.

35. (Amended) The gate electrode of claim 34 wherein said thin first spacers comprise an oxide.

36. (Amended) The gate electrode of claim 35 wherein said thin second spacers comprise a nitride.

37. (Amended) The gate electrode of claim 36 wherein said thin third spacers comprise an oxide.

38. (Amended) The gate electrode of claim 37 wherein said thick fourth spacers comprise a nitride.

39. (Amended) The gate electrode of claim 38 wherein said polycide comprises titanium salicide (TiSi_2).